

Novel Quantum Spin Assisted Tunneling in Half Metallic Manganite Tunnel Junctions

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The electron tunneling in half metallic manganite tunnel junctions is studied by using a quantum mechanically treated double exchange model. We show that the stimulation of spin excitations, caused by the strong Hund's coupling between the conduction e_g electrons and the localized quantum spins of the manganite ions, would assist electrons to tunnel through the junction even with the antiparallel aligned magnetizations of the electrodes. This mechanism gives rise to an extra tunnel conductance, in addition to that predicted by Julliere's model. Our theory is in good agreement with the voltage dependence of the tunnel conductance in manganite tunnel junctions observed by experiments.

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Tunnel magnetoresistance (TMR) in ferromagnetic junctions (FJ), first identified more than two decades ago [1], is of both fundamental interest and potential applications to magnetic sensors and memory devices. A simple model [1] proposed by Julliere is widely adopted to account for the observed TMR, in which the conductance of the polarized electrons are proportional to the product of the density of states (DOS) at the Fermi level from both magnetic electrodes for each spin channel. According to this model, the TMR ratio is given by

$$\frac{\Delta R}{R} = \frac{R_{AP} - R_P}{R_P} = \frac{2P^2}{1 - P^2}, \quad (1)$$

where R_P and R_{AP} are the tunnel resistances when the magnetizations of the two ferromagnetic electrodes are in parallel (P) and antiparallel (AP) alignments. P here is the spin polarization of the electrodes. This model works quite well for Fe, Co and Ni based ferromagnets. From Eq. (1) the TMR ratio tends to become infinity when the electrodes are made of half-metallic ferromagnets where only one spin component exists and $P = 1$, such as in some mixed valence manganites $\text{La}_{1-x}\text{A}_x\text{MnO}_3$, (A=Ca, Ba, Sr, etc.). The bulk of these manganese oxides, well known as the colossal magnetoresistance (CMR) materials, have been intensively studied in recent years. The involved physics is based on the double exchange (DE) model [2-4] which can be described by the following Hamiltonian

$$H = -t \sum_{ij,\sigma} c_{i\sigma}^\dagger c_{j\sigma} - J_H \sum_i \vec{S}_i \cdot \vec{\sigma}_i, \quad (2)$$

where the two terms represent the conduction e_g electron hopping between neighboring Mn ions and the on-site Hund's coupling between the electron spin $\vec{\sigma}$ and the localized t_{2g} core spin $\vec{S}_i$ of Mn^{3+} . It is well known that in mixed valence manganite system the strong Hund's coupling $J_H \gg t$ dominates the basic physics by separating the two spin subbands. The even stronger on-site Coulomb repulsion (not written out in Eq. (2)) further enhances the energy difference between the two subbands. As a result, a reasonable assumption of a full spin

polarization ($P = 1$) was extensively accepted in the literatures. For this reason, the manganese oxides have been recognized as being good candidates for the study of various spin polarized tunnelings [5-9]. The authors in Refs. [6-8] fabricated FJ using $\text{La}_{0.67}\text{Sr}_{0.33}\text{MnO}_3$, $\text{La}_{0.8}\text{Sr}_{0.2}\text{MnO}_3$ and $\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$ to obtain a high TMR ratio 80%, 150%, and 430% respectively [6-8]. More recently, a TMR ratio as high as 730% are obtained by Jo et al. with $\text{La}_{0.7}\text{Ca}_{0.3}\text{MnO}_3$ as electrodes [9]. All these results were explained by Julliere's model, from which a spin polarization $P = 0.54, 0.65, 0.83$ and 0.88 are respectively assumed. While these values are much larger than that of a typical common magnetic transition metal, they are still far away from the expected $P = 1$ for half-metallic manganites. Furthermore, it is found that the tunnel conductance G in these manganite junctions depends on the bias voltage V . In both the P and AP magnetization alignments, G has a considerable increase when V rises up to tens of mV [5-9]. As a result, TMR is strongly reduced. Bratkovsky attributed the V -dependence of G to the lowering of the barrier height of the insulator layer by the applied voltage, but his calculation shows that this effect becomes appreciable only when $|eV| > 0.3\text{eV}$ [10]. Therefore the origin of such a voltage dependence of the conductance can not be explained by the existing theories [1,10] and so far still is a puzzle. To account for the discrepancy between the expected full spin polarization of the observed finite TMR ratio, it was proposed that the presence of defect states in the barrier or resonant state can reduce the TMR [10]. A reduced TMR was also obtained by Lyu et al. who introduced spin-flip matrix elements in the tunneling Hamiltonian [11]. Recently, Itoh et al. also studied the effect of the temperature dependence of the spin polarization on TMR [12].

In this work, we investigate the voltage-dependent electronic tunneling in the half-metallic manganite junctions based on a quantum mechanical treatment of the DE model. It is found that in the AP aligned electrodes even without any spin-flip scattering from the tunnel-

ing Hamiltonian, an electron can still tunnel through the junction resulting in a nonzero conductance and thus finite TMR. Such a tunneling comes from the intrinsic quantum spin effect, and is accompanied by the stimulation of spin excitations in the ferromagnetic electrodes. In the classical spin $S \rightarrow \infty$ limit, our result reduces to a formula similar to that of Julliere's model. For finite S , the quantum spin effect becomes prominent and suppresses strongly the TMR amplitude. We show that our theory explains well the voltage dependence of the tunnel conductance in manganite tunnel junctions observed in Refs. [6] and [8].

We start from the following model for manganite tunnel junctions

$$H = H_L + H_R + H_T, \quad (3)$$

where H_L and H_R are the quantum DE Hamiltonian with the form of Eq. (2) in the left and right electrodes. H_T represents the spin-conserved incoherent tunneling process of conduction electrons through the insulator barrier. In the momentum space, it is given by

$$H_T = \sum_{pp',\sigma} (T_{pp'} c_{p'\sigma}^{R\dagger} c_{p\sigma}^L + h.c.). \quad (4)$$

According to the perturbation theory, the net electronic tunnel current is

$$I = \frac{2\pi e}{\hbar} \mathcal{Z}^{-1} \sum_{m,n} \sum_{pp',\sigma} |\langle n | T_{pp'} c_{p'\sigma}^{R\dagger} c_{p\sigma}^L | m \rangle|^2 \times (e^{-\beta E_m} - e^{-\beta E_n}) \delta(E_n - E_m + eV), \quad (5)$$

where $|m\rangle$, $|n\rangle$ are eigenstates of $H_L + H_R$ with energy E_m and E_n , $\mathcal{Z} = \text{Tr} e^{-\beta(H_L + H_R)}$, with $\beta = (k_B T)^{-1}$ the inverse temperature, and V is the applied bias voltage. The delta function ensures the conservation of energy in the tunneling process.

To derive the tunnel current from Eq. (5), it is convenient to use the Schwinger-boson or slave-fermion representation [13,14] in which the electron operator $c_{i\sigma}$ is expressed as a combination of a spinless charge fermion f_i and a neutral spin boson $b_{i\sigma}$. In the present strong Hund's coupling ($J_H \rightarrow \infty$) case, the spin of an electron on a site is aligned parallelly to the local spin, and the electron operator can be written as $c_{i\sigma}^L = f_i^L b_{i\sigma}^L / \sqrt{2S_L + 1}$ for $i \in L$, and $c_{i\sigma}^R = f_i^R \sum_{\sigma'} U_{\sigma\sigma'}(\theta) b_{i\sigma'}^R / \sqrt{2S_L + 1}$ for $i \in R$, where $S_L = 3/2$ is the local spin at the site i , and $U_{\sigma\sigma'}(\theta)$ are matrix elements of the 2×2 matrix $U(\theta) = \cos(\theta/2) \hat{1} + i \sin(\theta/2) \sigma_y$. Without loss of generality, we assume the magnetization in the left electrode is parallel to the z-axis while the magnetization in the right electrode makes an arbitrary angle θ with the z-axis. $\theta = 0$ and π correspond to the P and AP configurations of the junction magnetizations. The total spin of a site (the local spin plus the spin of the itinerant electron) is $\vec{S}_i^{\text{tot}} = \frac{1}{2} \sum_{\sigma\sigma'} b_{i\sigma}^\dagger \vec{\sigma}_{\sigma\sigma'} b_{i\sigma'}$, with the local constraint

$\sum_{\sigma} b_{i\sigma}^\dagger b_{i\sigma} = 2S_L + f_i^\dagger f_i$. We use a mean-field approximation that was derived in Ref. [14] for the unperturbed Hamiltonian H_α ($\alpha = L, R$)

$$H_\alpha = \sum_k \epsilon_k f_k^{\alpha\dagger} f_k^\alpha + \sum_k \omega_k b_{k\sigma}^{\alpha\dagger} b_{k\sigma}^\alpha, \quad (6)$$

where $\omega_k = \rho k^2$, with the spin stiffness $\rho = \rho_0 \{1 - \sum_k \gamma_k [\exp(\beta \rho_0 \gamma_k) - 1]^{-1} / 12S\}$, and $\epsilon_k = \bar{t}(\gamma_k - 6)$ with $\bar{t} = t \sum_{\sigma} \langle b_{i\sigma}^\dagger b_{j\sigma} \rangle / 2S$. Here $\rho_0 = t \langle f_i^\dagger f_j \rangle / 2S$, $\gamma_k = 6 - 2(\cos k_x + \cos k_y + \cos k_z)$ and $S = S_L + (1 - x)/2$ is the average spin per site. The total number of spin bosons is $n_\uparrow + n_\downarrow = 2NS$, where $n_\sigma = \sum_k \langle b_{k\sigma}^\dagger b_{k\sigma} \rangle$ and N is the total number of sites. At temperatures below the Curie temperature T_c and at each electrode, there are macroscopic numbers of bosons condense into $\vec{k} = 0$ and $\sigma = \uparrow$ state, $n_{0,\uparrow} = n_\uparrow - n_\downarrow = 2NSm$, where $m = (n_\uparrow - n_\downarrow) / (n_\uparrow + n_\downarrow) = M/M_s$, with M the magnetization of the electrode and M_s its saturation value, is just the normalized magnetization of the electrode. Employing the Schwinger boson representation for Eq. (5) and after some algebra, we obtain the following tunnel current

$$I = \frac{2\pi e |\bar{T}|^2}{\hbar (2S_L + 1)^2 N^2} \sum_{qq'} \sum_{k\sigma, k'\sigma'} |U_{\sigma\sigma'}(\theta)|^2 \times [n_q^f n_{k\sigma}^b (1 - n_{q'}^f) (n_{k'\sigma'}^b - (1 - n_q^f) (n_{k\sigma}^b + 1) n_{q'}^f n_{k'\sigma'}^b)] \times \delta(\epsilon_q + \omega_k - \epsilon_{q'} - \omega_{k'} + eV), \quad (7)$$

where $n_q^f = [e^{\beta(\epsilon_q - \epsilon_F)} + 1]^{-1}$ and $n_{k\sigma}^b = (e^{\beta\omega_k} - 1)^{-1}$ are the distribution functions of charge fermions and spin bosons. In the derivation we have treated $|T_{pp'}|^2$ as a constant $|\bar{T}|^2$. Taking into account the condensation of the spin bosons in the $\vec{k} = 0$ and $\sigma = \uparrow$ state, and that the band width of the fermion is in the order of electron volts much larger than energy scales of $k_B T$ and eV , thus the DOS of fermions near the Fermi level is approximated as a constant, the dynamical conductance of the junction $G = dI/dV$ can be derived as

$$G(\theta) = \frac{1}{2} G_0 \{1 + m^2 \cos \theta + \frac{1-m}{S} + \frac{m}{S} \int_0^{e|V|} g_b(\omega) d\omega + \frac{1}{S^2} \int_0^{\omega_m} g_b(\omega) d\omega \int_0^{\omega + e|V|} [n^b(\omega) - n^b(\omega')] g_b(\omega') d\omega'\}, \quad (8)$$

where $G_0 = \frac{2\pi e^2}{\hbar} (\frac{2S}{2S_L + 1})^2 |\bar{T}|^2 g_f^2(\epsilon_F)$ with $g_f(\epsilon)$ the DOS of fermions, $n^b(\omega) = (e^{\beta\omega} - 1)^{-1}$, $\omega_m = (6\pi^2)^{2/3} \rho$ is the maximum energy of the spin excitation, and $g_b(\omega)$ is the normalized DOS of bosons, i.e., $\int_0^{\omega_m} g_b(\omega) d\omega = 1$.

Eq. (8) is the tunnel conductance of the half-metallic manganite for arbitrary magnetization configuration, in which a voltage dependence is found in the last two terms. All the last three terms are related to the spin size S and vanish when the spin is treated classically

($S \rightarrow \infty$). This indicates that they come from the quantum spin effect. In the classical spin limit the TMR reduces to $\Delta R/R = 2m^2/(1 - m^2)$, which has a similar form to Julliere's formula Eq. (1), but the spin polarization P there is replaced by the normalized magnetization m here. P and m are usually different, the former is the relative difference of the DOS at the Fermi level between the two electron subbands split by the Hund's coupling, in the large J_H limit it is always 1 (see, e.g., the calculation of P in Ref. [12]) so the system is half-metallic, while the latter reaches 1 only at zero temperature, and decreases with the increase temperature due to the spin wave excitations. When the quantum spin effect is taken into account, even at zero temperature with full magnetization ($m=1$), the fourth term contributes a nonzero conductance. In the application of a small voltage $e|V| < \omega_m$, this term reduces to $(e|V|/\rho)^{3/2}/6\pi^2 S$, so that our theory predicts the tunnel conductance $G(\theta)$ at low temperatures behaves as $A + B|V|^{3/2}$, where A, B are constants independent of V . In Fig. 1(a) we show a comparison between our theory and experimental data in Ref. [6] in the AP magnetization configuration of the $\text{La}_{0.67}\text{Sr}_{0.33}\text{MnO}_3/\text{SrTiO}_3/\text{La}_{0.67}\text{Sr}_{0.33}\text{MnO}_3$ junction at $T = 4.2\text{K}$. The electronic hopping t is taken to be 0.35 eV so that $\rho \approx 14\text{meV}$. Apart from the difference of a small voltage-independent constant, which may come from spin-flip centers, defect states in the barrier, $m < 1$ at finite temperature or imperfect alignment of moments in a less-than-ideal sample [10,11], our calculated conductance is in excellent agreement with the experimental measurement. For comparison the conductance in the classical spin treatment ($S = \infty$) of the DE model is also plotted by the dashed line, which is independent of V . The dependence of the conductance on voltage also indicates that we have to specify the value of the bias voltage when discussing the TMR. Interestingly, for the case of $e|V|$ larger than the band width of spin excitations, both the fourth and the last terms in Eq. (8) become independent of the bias voltage. While further increasing of the conductance with the rise of the voltage may be still possible through lowering the energy barrier of the insulator layer [10], such an increase does not change the ratio of TMR. From Eq. (8) and under this large voltage, the TMR ratio in the full magnetization $m = 1$ of an ideal half metallic manganite junction is $\Delta R/R = 2S$, which is less than 400% for realistic $S < 2$. A divergent TMR ratio can be obtained only when S is treated as classically ($S \rightarrow \infty$) so that the quantum spin effect induced tunneling vanishes and the conductance in the AP magnetization configuration goes to zero.

The effect of temperature comes into the conductance mainly through the normalized magnetization m , which decreases with increasing the temperature. In Fig. 1(b) we plot the voltage-dependent conductance at different temperatures. To compare our calculations with the experimental results in Ref. [8] in which the FJ

was $\text{La}_{0.8}\text{Sr}_{0.2}\text{MnO}_3/\text{SrTiO}_3/\text{La}_{0.8}\text{Sr}_{0.2}\text{MnO}_3$, we need to determine the magnetizations at different temperatures. Here the magnetizations are estimated from the measurement in Ref. [15], they are taken as $m = 1$ at $T = 0$, $m = 0.6$ at $T = 0.4T_c$, and $m = 0.2$ at $T = 0.8T_c$, with $T_c = 290\text{K}$ [8]. In Fig. 1(b) at each temperature we shift the voltage-independent constant conductance so that the comparison of the V -dependent conductance at different temperatures can be shown more clearly. Fig. 1(b) shows that the increase of the conductance with the increasing voltage becomes slower at higher temperatures, in agree with the experimental results of Ref. [8].

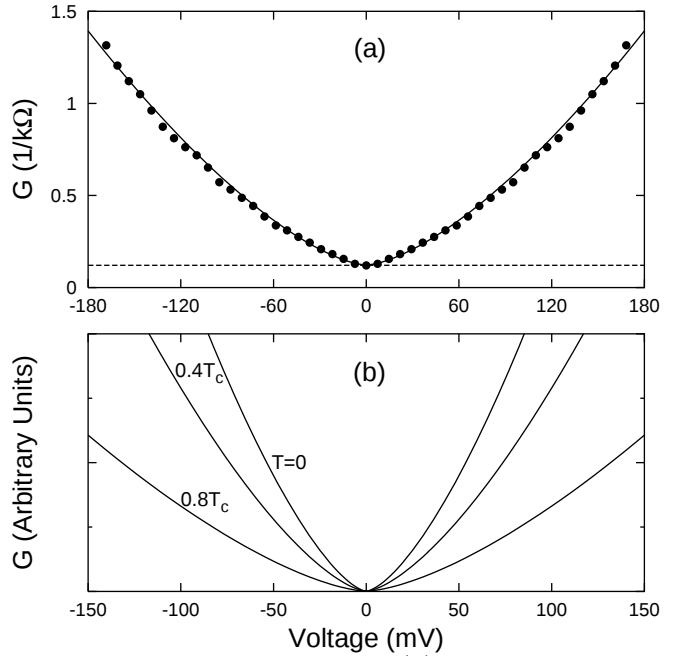


FIG. 1. Tunnel conductance $G(\pi)$ as a function of the applied voltage (a) at temperature $T = 4.2\text{K}$ and doping $x = 0.33$, where the conductance has been shifted a small voltage-independent constant so as to compare with the experimental measurement of Ref. [6], which is shown by the dots in the present figure, and G_0 in Eq. (8) is taken to be $6.11 (k\Omega)^{-1}$, the dashed line is for $S = \infty$, which is voltage independent, (b) at temperatures $T = 0, 0.4T_c$ and $0.8T_c$ and $x = 0.2$, with $T_c = 290\text{K}$. The electron hopping is taken to be $t = 0.35\text{eV}$.

At this stage, we wish to address on why it is possible for electrons to tunnel through the junction for a spin conserved tunneling Hamiltonian when the magnetizations of the two fully polarized electrodes are antiparallel to each other. Although the Schwinger boson method is convenient for calculation, the spin boson operator in it describes the total spin on a site as a whole, which conceals the actual motion of different spins. To see the physical origin of the nonvanishing $G(\pi)$, we now start directly from the DE Hamiltonian Eq. (2). At each site the Hund's coupling $-J_H \vec{S}_i \cdot \vec{\sigma}_i$ has two eigenvalues $-J_H S_l$

and $J_H(S_l + 1)$, where the former is $2S_l + 2$ fold degeneracy with total spin $S_l + 1/2$, and the latter is $2S_l$ degeneracy with total spin $S_l - 1/2$. In the case of the strong Hund's coupling, at an occupied site only the lower energy state can exist, i.e., the spin of the electron must be parallel to the local spin. In this case, the effective DE hopping of the e_g electrons between two neighboring sites is usually treated to be $t_{eff} = t \cos \theta_{ij}$ [2], where θ_{ij} is the relative angle between local spins on the two sites. When the effective hopping is generalized to manganite junctions with AP configuration at zero temperature, $\theta_{ij} = \pi$ for i and j in different electrodes, and the electron can not tunnel through the junction. That is exactly what Julliere's model predicts. However, such a classical picture neglects the quantum nature of local spins. In fact, when the quantum effect is taken into account, the spin of a conduction electron in one electrode can not be perfectly antiparallel to a localized spin in the other electrode. For example, when a spin-up ($s_z = 1/2$) electron in the left electrode moves to a spin-down site ($S_z = -S_l$) in the right electrode, the formed $|1/2, -S_l\rangle$ state, which is not an eigenstate of the Hund's coupling, has nonzero components in both the spin parallel (the e_g electron spin and the local spin are in parallel) and spin antiparallel subspaces. Using the method of projection operator, it is straightforward to show

$$|\frac{1}{2}, -S_l\rangle = \sqrt{\frac{1}{2S_l + 1}} |\psi_p\rangle + \sqrt{\frac{2S_l}{2S_l + 1}} |\psi_{ap}\rangle, \quad (9)$$

where $|\psi_p\rangle = (|1/2, -S_l\rangle + \sqrt{2S_l} | -1/2, -S_l + 1\rangle) / \sqrt{2S_l + 1}$ and $|\psi_{ap}\rangle = (\sqrt{2S_l} |1/2, -S_l\rangle - | -1/2, -S_l + 1\rangle) / \sqrt{2S_l + 1}$ are states in which the electron spin and the local spin are in parallel and antiparallel. Both $|\psi_p\rangle$ and $|\psi_{ap}\rangle$ are eigenstates of $\hat{S}_{tot}^z$ (z-component of the total spin of the site) with eigenvalues $-S_l + 1/2$. At the same time, they are also eigenstates of the Hund's coupling $-J_H \vec{S}_i \cdot \vec{\sigma}_i$, with eigenvalues $-J_H S_l$ for $|\psi_p\rangle$ and $J_H(S_l + 1)$ for $|\psi_{ap}\rangle$. For large J_H , state $|\psi_{ap}\rangle$ is forbidden due to its very high energy. However, Eq. (9) shows that $|1/2, -S_l\rangle$ has a nonzero component in $|\psi_p\rangle$, i.e., there is a finite probability $1/(2S_l + 1)$ for the spin of a spin-up electron to be parallel to a spin-down local site, so that even in this $J_H \rightarrow \infty$ case the electron may still tunnel through the junction. This tunneling process vanishes when $S_l \rightarrow \infty$, which is an implication that this effect is induced by the quantum nature of the localized spins. In the second term of $|\psi_p\rangle$, the spin of the electron is flipped while the local spin of the site is twisted. Such a spin-flip and spin-twist process is an intrinsic dynamic effect originated from the Hund's coupling and the discrete quantum spin orientations. Moreover, the twist of the local spin can spread to the whole system to further lower the energy, thus stimulates a spin excitation and enables electrons to tunnel through the barrier. This mechanism is very different from that considered in some other pa-

pers [11,16,17]. The energy scale involved in this tunneling process is the spin excitation energy which comes from the applied voltage and thus causes the induced tunneling to be voltage dependent.

Finally, it is worth to mention that in some experiments, at temperatures 77K and above, a quadratic variation of the conductance with the applied voltage was found [7,9]. This is likely due to the fact that the DOS of the spin excitations near the ferromagnet/insulator (F/I) regions is different from that in the bulk manganites. Experimental study of the magnetic properties at surface boundary of the half-metallic ferromagnet $\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$ indeed indicates that except at very low temperature ($T < 30\text{K}$), the temperature dependence of the surface-boundary magnetism is significantly different from that of the bulk [15]. In the present theory, a V^2 dependence of the conductance can be produced if the spin excitation spectrum has the form $\omega_k = \rho_{\parallel} k_{\parallel}^2 + \rho_{\perp} |k_{\perp}|$, where $k_{\parallel}$ and $k_{\perp}$ are the wave vectors in and perpendicular to the plane of the F/I interface, respectively. Such a dispersion relation was proposed for the lightly doped $\text{La}_{1-x}\text{Sr}_x\text{MnO}_3$ with layered antiferromagnetic spin alignment [18], and it may exist in the F/I interface regions of the half metallic manganite junctions.

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